

TRANSMITTAL OF INFORMATION DISCLOSURE STATEMENT**(Under 37 CFR 1.97(b) or 1.97(c))**Docket No.
FIS920020134US2In Re Application Of: **OMER DOKUMACI ET AL.**Serial No.
10/605,697Filing Date
10/21/2003Examiner
NYAGroup Art Unit
NYATitle: **GATE STRUCTURE WITH INDEPENDENTLY TAILORED VERTICAL DOPING PROFILE**

Address to:

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450**37 CFR 1.97(b)**

1. ☒ The Information Disclosure Statement submitted herewith is being filed within three months of the filing of a national application other than a continued prosecution application under 37 CFR 1.53(d); within three months of the date of entry of the national stage as set forth in 37 CFR 1.491 in an international application; before the mailing of a first Office Action on the merits, or before the mailing of a first Office Action after the filing of a request for continued examination under 37 CFR 1.114.

37 CFR 1.97(c)

2. ☐ The Information Disclosure Statement submitted herewith is being filed after the period specified in 37 CFR 1.97(b), provided that the Information Disclosure Statement is filed before the mailing date of a Final Action under 37 CFR 1.113, a Notice of Allowance under 37 CFR 1.311, or an Action that otherwise closes prosecution in the application, and is accompanied by one of:
- ☐ the statement specified in 37 CFR 1.97(e);
- OR**
- ☐ the fee set forth in 37 CFR 1.17(p).

TRANSMITTAL OF INFORMATION DISCLOSURE STATEMENT

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GATE STRUCTURE WITH INDEPENDENTLY TAILORED VERTICAL DOPING PROFILE**Payment of Fee**

(Only complete if Applicant elects to pay the fee set forth in 37 CFR 1.17(p))

- ☐ A check in the amount of _____ is attached.
- ☐ The Director is hereby authorized to charge and credit Deposit Account No. _____ as described below.
- ☐ Charge the amount of _____
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Signature

Dated: 10/23/2003

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 <p style="text-align: center;">INFORMATION DISCLOSURE CITATION (Use several sheets if necessary)</p>	Docket Number (Optional) FIS920020134US2	Application Number 10/605,697
	Applicant(s) OMER DOKUMACI ET AL.	
	Filing Date 10/21/2003	Group Art Unit NYA

U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE

FOREIGN PATENT DOCUMENTS

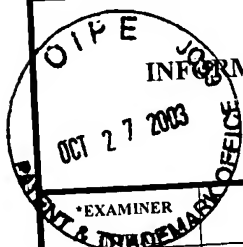
	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
							YES	NO

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

1	V. L. Rideout; "Fabricating Low Resistance Interconnection Lines and FET Gates in a Single Step;" IBM Technical Disclosure Bulletin, Vol. 21, No. 3, August 1978; pages 1250 - 1251.
2	Mitra Navi and Scott T. Dunham; "Investigation of Boron Penetration Through Thin Gate Dielectrics Including Role of Nitrogen and Fluorine;" J. Electrochem. Soc., Vol. 15, No. 7, July 1998; pages 2545 - 2458

EXAMINER	DATE CONSIDERED
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EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.



INFORMATION DISCLOSURE CITATION
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OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

Richard B. Fair, "Modeling Boron Diffusion in Ultrathin Nitrided Oxide p+ Si Gate Technology," IEEE Electron Device Letters, Vol. 18, No. 6, June 1997; pages 244 - 247.

3

EXAMINER

DATE CONSIDERED

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